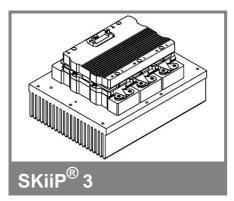
## SKiiP 513GD172-3DUL



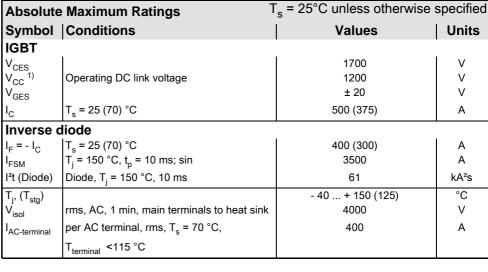
## 6-pack-integrated intelligent Power System

### Power section SKiiP 513GD172-3DUL

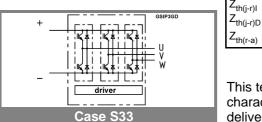
**Preliminary Data** 

#### **Features**

- SKiiP technology inside
- Trench IGBTs
- CAL diode technology
- · Integrated current sensor
- Integrated temperature sensor
- Integrated heat sink
- IEC 60721-3-3 (humidity) class 3K3/IE32 (SKiiP® 3 System)
- IEC 60068-1 (climate) 40/125/56
- UL recognized file no. E63532
- with assembly of suitable MKP capacitor per terminal (SEMIKRON type is recommended)



$ \begin{array}{c ccccccccccccccccccccccccccccccccccc$	$\begin{array}{c} \text{V} \\ \text{V} \\ \text{m}\Omega \\ \text{mA} \end{array}$
$\begin{array}{c ccccccccccccccccccccccccccccccccccc$	V mΩ
$ \begin{array}{c ccccccccccccccccccccccccccccccccccc$	V mΩ
$ \begin{array}{c ccccccccccccccccccccccccccccccccccc$	mΩ
$ \begin{array}{c ccccccccccccccccccccccccccccccccccc$	
T <sub>i</sub> = 25 (125) °C	mA
$E_{on} + E_{off} = 300 \text{ A}, V_{CC} = 900 \text{ V}$ 195	mJ
$T_j = 125 ^{\circ}\text{C},  V_{CC} = 1200 ^{\circ}\text{V}$ 288	mJ
$R_{CC+EE'}$ terminal chip, $T_j = 25  ^{\circ}C$ 0,5	mΩ
L <sub>CE</sub> top, bottom 12	nΗ
C <sub>CHC</sub> per phase, AC-side 1,7	nF
Inverse diode	
$V_F = V_{EC}$ $I_F = 300 \text{ A}, T_j = 25 (125) ^{\circ}\text{C}$ 1,9 (1,7) 2,4 measured at terminal	V
$V_{TO}$ $T_j = 25 (125) °C$ 1,1 (0,8) 1,4 (1,1)	V
$r_{T}$ $T_{i} = 25 (125) ^{\circ}C$ $2,6 (2,9) 3,4 (3,7)$	mΩ
$E_{rr}$ $I_C = 300 \text{ A}, V_{CC} = 900 \text{ V}$ 36	mJ
$T_j = 125 ^{\circ}\text{C},  V_{CC} = 1200 ^{\circ}\text{V}$ 43	mJ
Mechanical data	
M <sub>dc</sub> DC terminals, SI Units 6	Nm
M <sub>ac</sub> AC terminals, SI Units 13	Nm
w SKiiP® 3 System w/o heat sink 2,4	kg
w heat sink 7,5	kg
Thermal characteristics (PX 16 heat sink with fan SKF16B-230-1); "s"	
reference to heat sink; "r" reference to built-in temperature sensor (a	cc.IEC
60747-15)	12001
R <sub>th(j-s)l</sub> per IGBT 0,059	K/W
R <sub>th(j-s)D</sub> per diode 0,115	K/W
Z <sub>th</sub> R <sub>i</sub> (mK/W) (max. values) tau <sub>i</sub> (s)	
1 2 3 4 1 2 3   10,2 28,8 21 0   363 0,18 0,04	4



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60

1,4

30

210

5

85

0,25

0,04

0,4

36

20

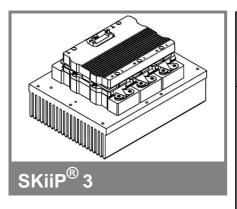
54

5,5

36

2,1

## SKiiP 513GD172-3DUL



# 6-pack-integrated intelligent Power System

6-pack integrated gate driver SKiiP 513GD172-3DUL

**Preliminary Data** 

#### Gate driver features

- CMOS compatible inputs
- Wide range power supply
- Integrated circuitry to sense phase current, heat sink temperature and

DC-bus voltage (option)

- Short circuit protection
- · Over current protection
- Over voltage protection (option)
- Power supply protected against under voltage
- Interlock of top/bottom switch
- Isolation by transformer
- IEC 60068-1 (climate) 40/85/56
- UL recognized file no. 242581

<b>Absolute Maximum Ratings</b> $T_a = 25^{\circ}\text{C}$ unless otherwise specifie					
Symbol	Conditions	Values	Units		
$V_{S2}$	unstabilized 24 V power supply	30	V		
$V_{i}$	input signal voltage (high)	15 + 0,3	V		
dv/dt	secondary to primary side	75	kV/μs		
$V_{isollO}$	input / output (AC, rms, 2s)	4000	V		
V <sub>isoIPD</sub>	partial discharge extinction voltage, rms, Q <sub>PD</sub> ≤10 pC;	1500	V		
V <sub>isol12</sub>	output 1 / output 2 (AC, rms, 2s)	1500	V		
f <sub>sw</sub>	switching frequency	14	kHz		
f <sub>out</sub>	output frequency for I=I <sub>C</sub> ; sin.	1	kHz		
$T_{op} (T_{stg})$	operating / storage temperature	- 40 <b>+</b> 85	°C		

Characteristics					$T_a = 25^{\circ}C$	
Symbol	Conditions	min.	typ.	max.	Units	
$V_{S2}$	supply voltage non stabilized	13	24	30	V	
I <sub>S2</sub>	V <sub>S2</sub> = 24 V	420+34*f/kHz+0,00015*(I <sub>AC</sub> /A) <sup>2</sup>			mA	
V <sub>iT+</sub>	input threshold voltage (High)			12,3	V	
$V_{iT-}$	input threshold voltage (Low)	4,6			V	
R <sub>IN</sub>	input resistance		10		kΩ	
C <sub>IN</sub>	input capacitance		1		nF	
t <sub>d(on)IO</sub>	input-output turn-on propagation time		1,3		μs	
t <sub>d(off)IO</sub>	input-output turn-off propagation time		1,3		μs	
t <sub>pERRRESET</sub>	error memory reset time		9		μs	
t <sub>TD</sub>	top / bottom switch interlock time		3,3		μs	
I <sub>analogOUT</sub>	max. 5mA; 8 V corresponds to 15 V supply voltage for external components		500		Α	
I <sub>s1out</sub>	max. load current			50	mA	
I <sub>TRIPSC</sub>	over current trip level (I <sub>analog</sub> OUT = 10 V)		625		Α	
$T_{tp} \ U_{DCTRIP}$	over temperature protection  U <sub>DC</sub> -protection ( U <sub>analog OUT</sub> = 9 V);  ()	110	1200	120	°C V	

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